

## ABSTRACT OF THE DISCLOSURE

A microelectronic device fabricating method includes providing a substrate having a mean global outer surface extending along a plane. A first portion is formed over the substrate comprising a straight linear segment which is angled from the plane and forming a second portion over the substrate comprising a straight linear segment which is angled from the plane at a different angle than the first portion. A layer of structural material is formed over the first and second portions. The structural material layer is anisotropically etched and a first device feature is ultimately left over the first portion having a first base width and a second device feature is ultimately left over the second portion having a second base width which is different from the first base width. Integrated circuitry includes a substrate having a mean global outer surface extending along a plane. The substrate includes a first conductive device component of a first type which is elongated in a first direction generally parallel with the plane. A second conductive device component of the first type is included which is elongated in a second direction generally parallel with the plane, with the first and second conductive device components at least predominately comprise common conductive material. The first and second conductive device components have different base widths. At least one of the first and second conductive device components is elevationally angled from perpendicular to the plane along at least a majority of its elongated length in its respective first or second direction.